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INFORMATION DISCLOSURE STATEMENT				Applicants: Shinji NAKAMURA et al.			
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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
Examiner Initial		S. Tomioka et al., "GaN Substrates with a Low Dislocation Density Grown by HVPE" In Extended Abstracts (The 61st Autumn Meeting, 2000), 9/3/00, Section 5p-Y-17, Japan Society of Applied Physics, Catalog No. AP001130-01					
bu		<div style="text-align: right;"> RECEIVED MAR 2 2001 2000 MAR 2 1000M </div> <div style="text-align: right;"> RECEIVED MAR 30 2001 TC 1100 MAIL ROOM </div>					
Examiner <i>Brown Kebede</i>		Date Considered <i>11/29/2002</i>					
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